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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/678,103	10/06/2003	Tsukasa Ooishi	67161-113	1069
75	90 03/14/2005		EXAMINER	
McDermott, Will Emery 600 13th Street, N.W. Washington, DC 20005-3096			DINH, SON T	
			ART UNIT	PAPER NUMBER
			2824	
	•		DATE MAILED: 03/14/2005	

Please find below and/or attached an Office communication concerning this application or proceeding.

				- <b>X</b>			
		Application No.	Applicant(s)	-0			
Office Action Summary		10/678,103	OOISHI, TSU	KASA			
		Examiner	Art Unit				
		son t dinh	2824				
Period f	The MAILING DATE of this communication reply	n appears on the cover	sheet with the correspondence	address			
THE - External filter - If the control of the contr	IORTENED STATUTORY PERIOD FOR R MAILING DATE OF THIS COMMUNICAT ensions of time may be available under the provisions of 37 C r SIX (6) MONTHS from the mailing date of this communicati e period for reply specified above is less than thirty (30) days of period for reply is specified above, the maximum statutory cure to reply within the set or extended period for reply will, by reply received by the Office later than three months after the med patent term adjustment. See 37 CFR 1.704(b).	ION. FR 1.136(a). In no event, howevon. , a reply within the statutory minir period will apply and will expire S statute, cause the application to	er, may a reply be timely filed num of thirty (30) days will be considered IX (6) MONTHS from the mailing date of the become ABANDONED (35 U.S.C. § 133)	his communication.			
Status							
1)	Responsive to communication(s) filed on	•		•			
2a)□		This action is non-fina	l.	•			
3)□	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.						
Disposit	ion of Claims						
5)[🖂	Claim(s) <u>1-8</u> is/are pending in the applica 4a) Of the above claim(s) is/are with Claim(s) <u>3 and 4</u> is/are allowed. Claim(s) <u>1,2 and 5-8</u> is/are rejected. Claim(s) is/are objected to. Claim(s) are subject to restriction a	thdrawn from considera					
Applicat	ion Papers			·			
10)⊠	The specification is objected to by the Example The drawing(s) filed on <u>06 October 2003</u> is Applicant may not request that any objection to Replacement drawing sheet(s) including the of The oath or declaration is objected to by the example of the properties of the properties of the example	s/are: a)⊠ accepted o to the drawing(s) be held i correction is required if the	n abeyance. See 37 CFR 1.85(a drawing(s) is objected to. See 3	a). 7 CFR 1.121(d).			
Priority	under 35 U.S.C. § 119						
	Acknowledgment is made of a claim for for All b) Some * c) None of:  1. Certified copies of the priority docu 2. Certified copies of the priority docu 3. Copies of the certified copies of the application from the International B	ments have been receivences have been receive priority documents have bureau (PCT Rule 17.2(	ved. ved in Application No ve been received in this Natio a)).	nal Stage			
Attachmer	nt(s)						
	ce of References Cited (PTO-892)		nterview Summary (PTO-413)				
3) 🛛 Infor	ce of Draftsperson's Patent Drawing Review (PTO-94 mation Disclosure Statement(s) (PTO-1449 or PTO/S er No(s)/Mail Date <u>10/6/03</u> .	SB/08) 5) <u></u>	Paper No(s)/Mail Date  Notice of Informal Patent Application Other: <u>East search history</u> .	(PTO-152)			

Art Unit: 2824

#### **DETAILED ACTION**

#### Priority.

Receipt is acknowledged of papers submitted under 35 U.S.C. 119(a)-(d), which papers have been placed of record in the file.

## Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

Claims 1, 5, 7-8 are rejected under 35 U.S.C. 102(e) as being anticipated by Hidaka (U.S. Patent No 6,635,934).

With respect to claim 1, Hidaka (see figure 19) discloses a memory device having operation modes of a first mode (active mode that includes a normal mode, also see figure 20) and a second mode (standby mode or power down mode, see figure 20), the meomory device comprising a main power supply line (30, figure 19), a sub power supply line (32, figure 19), a first switch (SWa, figure 19) connecting the sub power supply line (32) to the main power supply line (30) in the first mode (active mode, see column 24, lines 50-55) and disconnecting the sub power supply line (32) from the main power supply line (30) in the second mode (see figure 20 and column 24, lines 50-55),

Art Unit: 2824

an internal circuit (PQa, PQb, PQc, PQd, NQa, NQb, NQc, NQd) operating according to an input signal (IN, figure 19) in the first mode and entering a standby state in the second mode, the internal circuit including a first field effect transistor (NQa of PQb, or NQc, or PQd) having a gate insulating film with a predetermined thickness (namely Tox1) and kept in a non-conductive state in the second mode (NQa is OFF in the standby that is a second mode, see column 25, lines 6-11), a second field effect transistor (PQa, or NQb, or, PQc, or NQd) connected the main power supply line 30 (one end of transistor PQa is connected to the maim power supply line 30 as shown in figure 10) having a gate insulating film with a thickness (Tox2) greater than the predetermined thickness (Tox1) (see column 25, line 12-13) and kept in conductive state in the second mode (see column 24, lines 60-67).

With respect to claim 5, for the purpose of this rejection, an ITR transistor would be considered as a field effect transistor with a thick gate insulating film as shown by Hidaka in column 65, lines 55-57). Hidaka discloses a memory device having operation modes of self refresh and a normal mode (see column 65, lines 1-10) comprising a memory array of dynamic type (200, figure 80), a first internal circuit (205, figure 77) including at least one field effect transistor of first type (a transistor with thin gate insulating film as defined by Hidaka in column 67, lines 64-67), activates in the normal mode and inactivates in the self refresh mode (column 68, lines 3-30), and a second internal circuit (201 or 202) including at least one field effect transistor of a second type (an ITR transistor that includes in the timer 202 or refresh address counter 201, see column 69, lines 43-49) having a gate insulating film thicker than that of the first field

Art Unit: 2824

effect transistor and activated in the self refresh mode (see column 68, lines 52-60, when the timer issues a self refresh signal i.e. the transitors in such timer is ON or activated).

With respect to claims 7 and 8, figure 59A of Hidaka discloses a memory device comprising a signal line (150) precharged to a first potential (Vcc) in a standby state (see figure 59B), a first field effect transistor (NQ17) coupling to the signal line 150 to a second potential (ground, as shown in figure 59A), a second field effect transistor (PTR15) coupling the signal line 150 to the first potential (Vcc) in the standby state. Note that the transistor NQ17 has a thin gate insulating film (column 56, lines 52-53) and transistor PTR15 is an ITR transistor (transistor with thick gate insulating film as explained above). Also, the signal line 150 is a data line between a DRAM (storage data) and any external circuit (like a decoder, or peripheral circuit).

## Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 2 and 6 are rejected under 35 U.S.C. 103(a) as being unpatentable over Hidaka in view of Arimoto (U.S. Patent No 6,256,252).

Hidaka applied as above. Further, the reference of Hidaka clearly shows that a standby mode (power down mode) and an acive mode (normal mode). The difference

Art Unit: 2824

between Hidaka and claims 2 and 6 is that Hidaka is silent on the use of switch connected between a power supply and power supply line (any line that supply power to the device) so as to disconnect the power supply from the memory device in a deep power down mode (or sleep mode).

Arimoto (see figure 23) teaches that the use of a switch between a power supply (namely VDDM) and power supply line (the line between SWm and memory 80 in figure 23) so as to disconnect the power supply node from the power supply line in a sleep mode (or deep power down mode) for the purpose of reducing power consumption is well known in the memory art. Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify Hidaka by incorporating a switch between a power supply node and a power supply line in order to disconnect the power supply node from the power supply line for the purpose of reducing power consumption as taught by Arimoto.

## Allowable Subject Matter

Claims 3-4 are allowed.

The following is a statement of reasons for the indication of allowable subject matter:

The prior art of record fail to teach or suggest a memory device comprising a first internal circuit provided with a power supply potential in a first mode and a second mode, a second internal circuit activated in the first mode and including at least one field effect transistor of a first type, a transmission gate connecting an output of the second

Art Unit: 2824

internal circuit to an input node of the first internal circuit in a the first mode and disconnecting the output from the input node in the second mode, and including a field effect transistor of a second type having a gate insulating film thicker than that of the field effect transistor of the first type, and a third internal circuit including at least one field effect transistor of the second type, activated in the second mode and driving the input node.

#### Conclusion

The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

-Hidaka (U.S. Patent No 6,487,136) disclose a memory device having self refresh circuit and a precharge circuit.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Son Dinh whose telephone number is 571-272-1868. The examiner can normally be reached on 8am-5pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Richard Elms can be reached on 571-272-1869. The fax phone number for the organization where this application or proceeding is assigned is 571-273-1868.

Application/Control Number: 10/678,103 Page 7

Art Unit: 2824

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

S. Dinh March 8, 2005

> Son T. Dinh Primary Examinar

Macalle